(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization

International Bureau



(43) International Publication Date 23 September 2004 (23.09.2004)

PCT

(10) International Publication Number WO 2004/081261 A2

(51) International Patent Classification7:

C25D

(21) International Application Number:

PCT/JP2004/003040

(22) International Filing Date: 9 March 2004 (09.03.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data: 2003-065476

2003-208315

11 March 2003 (11.03.2003) 21 August 2003 (21.08.2003)

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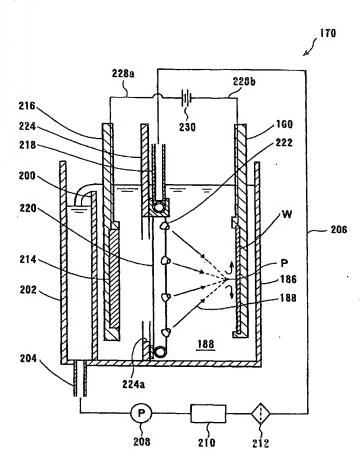
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,

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(54) Title: PLATING APPARATUS



(57) Abstract: The present invention is concerned with a plating apparatus for use in forming a plated film in trenches, via holes, or resist openings that are defined in a surface of a semiconductor wafer, and forming bumps to be electrically connected to electrodes of a package, on a surface of a semiconductor wafer. The plating apparatus (170) has a plating tank (186) for holding a plating solution (188), a holder (160) for holding a workpiece (W) and bringing a surface to be plated of the workpiece into contact with the plating solution (188) in the plating tank (186), and a ring-shaped nozzle pipe (220) disposed in the plating tank (186) and having a plurality of plating solution injection nozzles (222) for injecting the plating solution (188) to the surface to be plated of the workpiece held by the holder (160) to supply the plating solution (188) into the plating tank (186).

KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR,

GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

 without international search report and to be republished upon receipt of that report

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